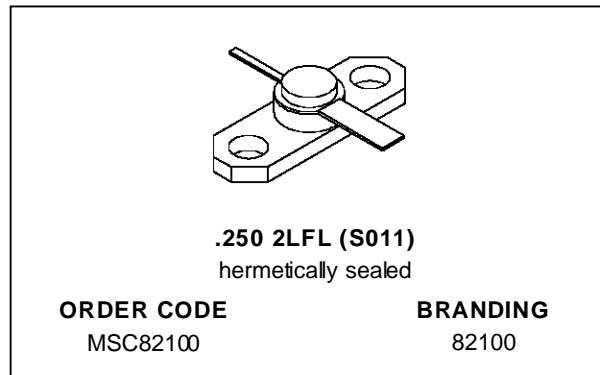


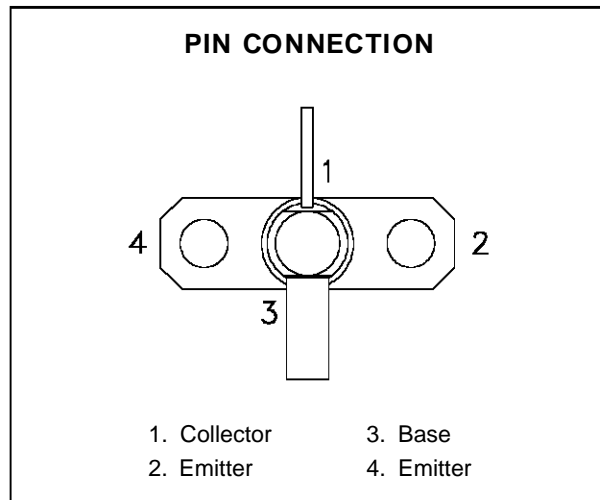
**RF & MICROWAVE TRANSISTORS
GENERAL PURPOSE LINEAR APPLICATIONS**

- EMITTER BALLASTED
- CLASS A LINEAR OPERATION
- COMMON EMITTER
- VSWR CAPABILITY $\infty:1$ @ RATED CONDITIONS
- ft 1.6 GHz TYPICAL
- NOISE FIGURE 15.5 dB @ 2 GHz
- P_{OUT} = 27 dBm MIN. @ 1.0 GHz



DESCRIPTION

The MSC82100 is a hermetically sealed NPN power transistor with a fishbone, emitter finger ballasted geometry utilizing a refractory/gold metallization system. The device is designed specifically for Class A linear applications to provide high gain and high output power at the 1.0 dB compression point.



ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
P _{DISS}	Power Dissipation (see Safe Area)	—	W
I _C	Device Bias Current	200	mA
V _{CE}	Collector-Emitter Bias Voltage*	20	V
T _J	Junction Temperature	200	°C
T _{STG}	Storage Temperature	- 65 to +200	°C

THERMAL DATA

R _{TH(j-c)}	Junction-Case Thermal Resistance*	20	°C/W
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*Applies only to rated RF amplifier operation

MSC82100

ELECTRICAL SPECIFICATIONS ($T_{\text{case}} = 25^{\circ}\text{C}$)

STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CBO}	$I_{\text{C}} = 1\text{mA}$	$I_{\text{E}} = 0\text{mA}$	45	—	—	V
BV_{EBO}	$I_{\text{E}} = 1\text{mA}$	$I_{\text{C}} = 0\text{mA}$	3.5	—	—	V
BV_{CEO}	$I_{\text{C}} = 5\text{mA}$	$I_{\text{B}} = 0\text{mA}$	20	—	—	V
I_{CEO}	$V_{\text{CE}} = 18\text{V}$		—	—	0.5	mA
h_{FE}	$V_{\text{CE}} = 5\text{V}$	$I_{\text{C}} = 100\text{mA}$	15	—	120	—

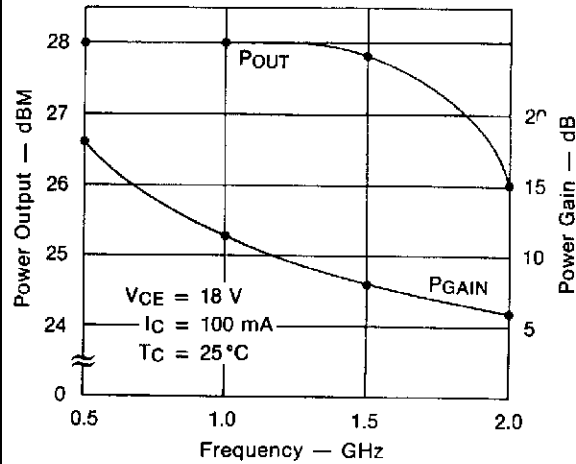
DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
G_{P}^*	$f = 1.0\text{ GHz}$	$P_{\text{OUT}} = 27\text{ dBm}$	10.5	11.5	—	dB	
ΔG_{P}^*	$f = 1.0\text{ GHz}$	$P_{\text{OUT}} = 27\text{ dBm}$	—	—	1	dB	
C_{OB}	$f = 1\text{ MHz}$	$V_{\text{CB}} = 28\text{ V}$	—	—	3.2	pF	

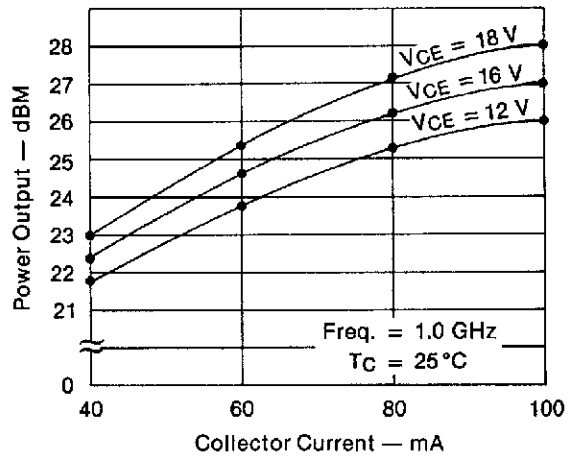
* Note: $V_{\text{CE}} = 18\text{V}$
 $I_{\text{C}} = 100\text{mA}$

TYPICAL PERFORMANCE

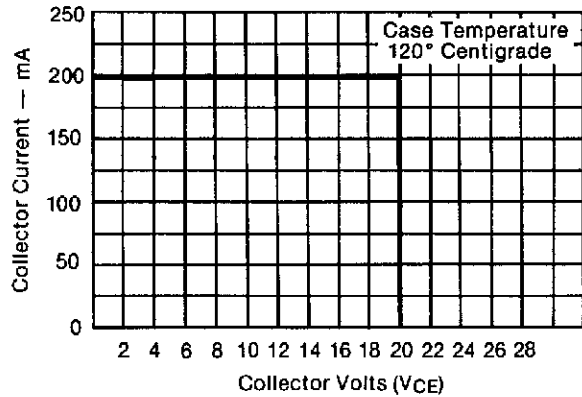
TYPICAL POWER OUTPUT & GAIN @ 1dB COMPRESSION POINT vs FREQUENCY



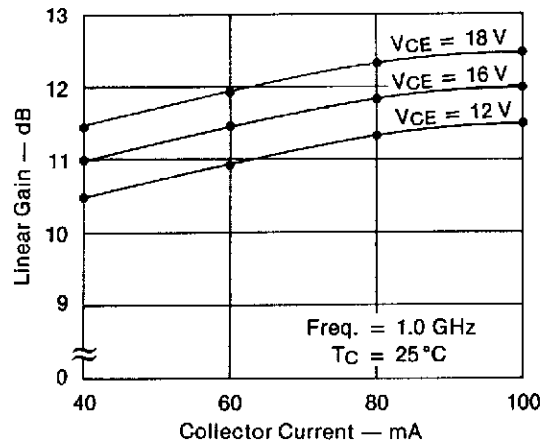
TYPICAL POWER OUTPUT & GAIN @ 1dB COMPRESSION POINT vs COLLECTOR CURRENT



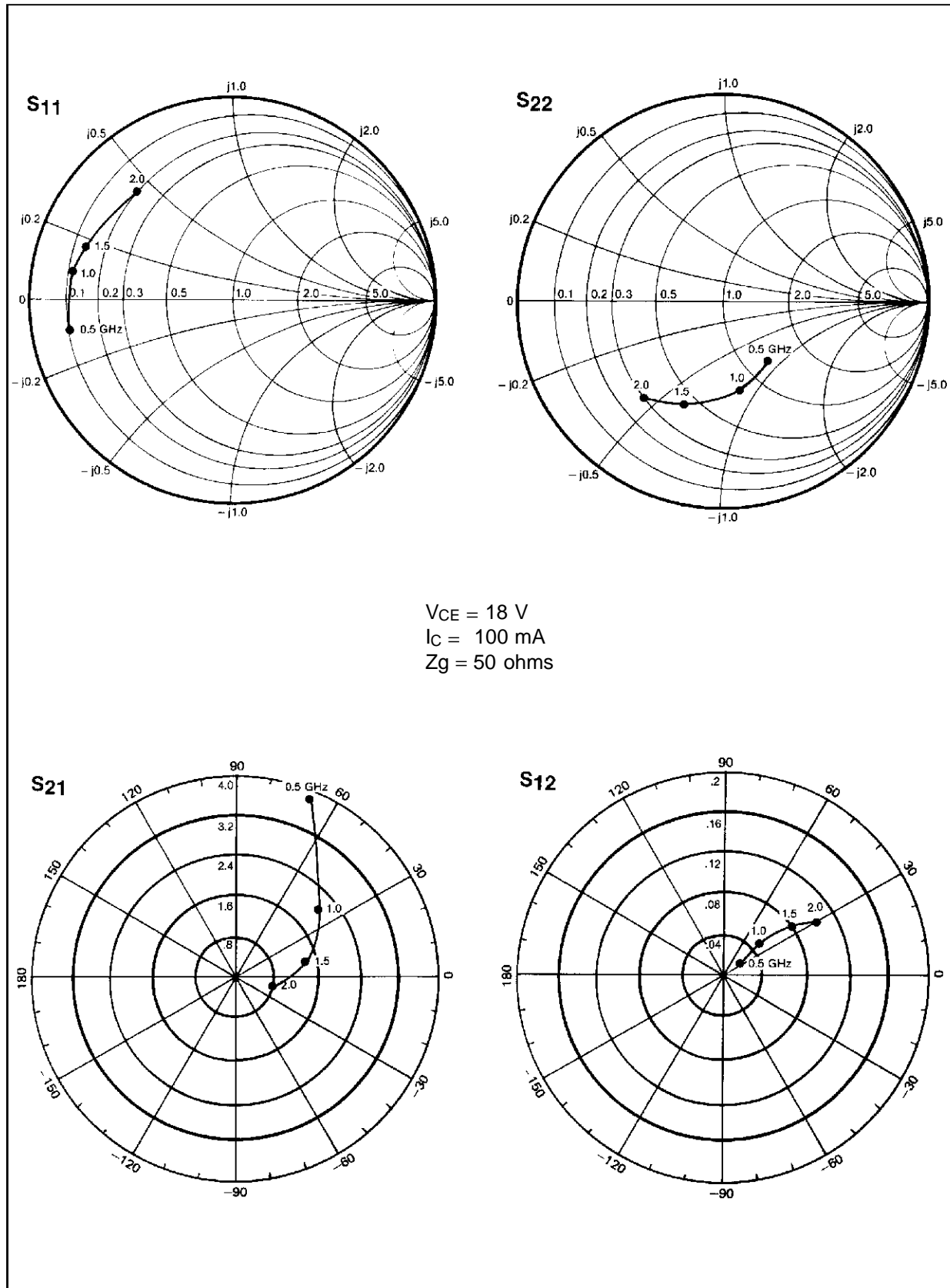
MAXIMUM OPERATING AREA FOR FORWARD BIAS OPERATION



TYPICAL LINEAR GAIN vs COLLECTOR CURRENT

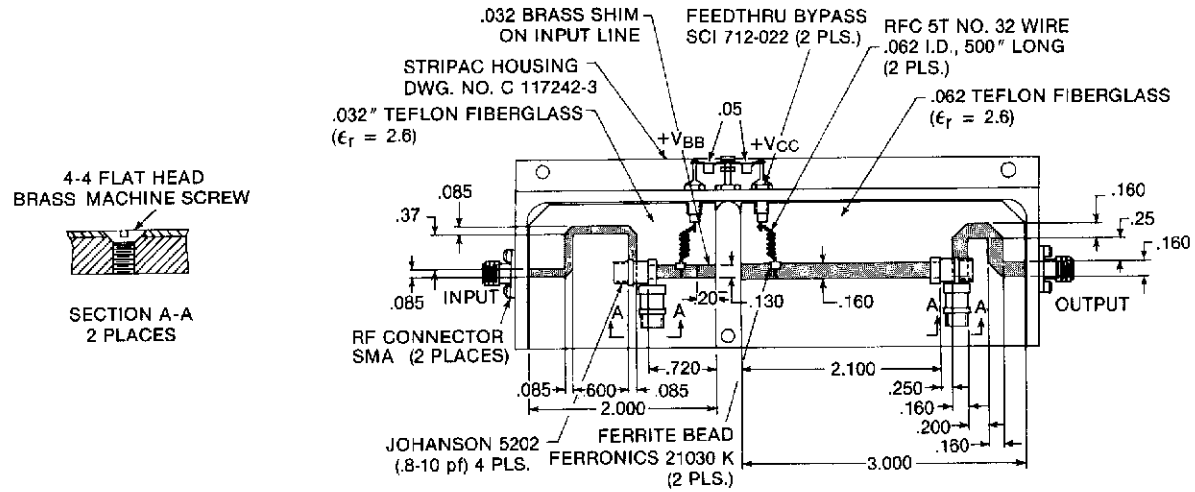


TYPICAL S-PARAMETERS



TEST CIRCUIT

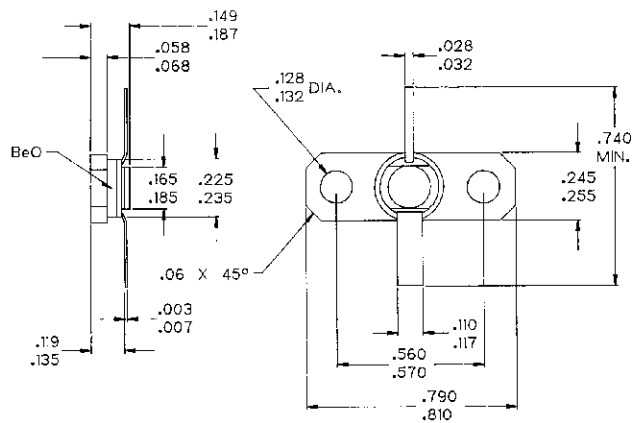
Ref.: Dwg. No. C127323



All dimensions are in inches.
 Frequency 1.0 GHz

PACKAGE MECHANICAL DATA

Ref.: Dwg. No.: J135021C



NOTES:
 1. ALL TOLERANCE $\pm .010$ EXCEPT WHERE NOTED;
 DIMENSIONS IN INCHES.

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